

## IN THE CLAIMS

Claims 1-12 are currently pending in the application. Claim 1 is an independent claim and claims 2-12 depend there from. Claim 7 is currently amended to overcome minor informalities noticed by the Examiner. The Applicant respectfully asserts that the minor amendment to claim 7 does not alter the scope of the claim as originally presented, but rather correct minor grammatical errors objected to by the Examiner.

Please amend the claims as follows.

1. (Original) A system for reducing noise in a chip, the system comprising:  
a substrate;  
a first well disposed on top of said substrate;  
a second well and a third well that are both disposed within said first well;  
a first transistor disposed in said second well;  
a quiet voltage source connected to a body of said first transistor; and  
a second transistor disposed in said third well.
2. (Original) The system according to claim 1, wherein said first transistor is a PMOS transistor.
3. (Original) The system according to claim 1, wherein said second transistor is an NMOS transistor.
4. (Original) The system according to claim 1, further comprising a noisy voltage source coupled to a source of said first transistor.
5. (Original) The system according to claim 1, wherein a body of said first transistor is resistively coupled to said second well.

6. (Original) The system according to claim 1, further comprising a noisy voltage source, wherein a body and a source of said second transistor are both coupled to said noisy voltage source.

7. (Currently Amended) The system according to claim 1, wherein said a body of said second transistor is capacitively coupled to said substrate.

8. (Original) The system according to claim 1, wherein said first well is a deep well.

9. (Original) The system according to claim 1, wherein said substrate is doped with a first dopant.

10. (Original) The system according to claim 1, wherein said first well is doped with a second dopant.

11. (Original) The system according to claim 1, wherein said second well is doped with a second dopant.

12. (Original) The system according to claim 1, wherein said third well is doped with a first dopant.